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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known			
		Application Number	10/804,430		
		Filing Date	03/19/2004		
		First Named Inventor	KIM ET AL.		
		Art Unit	1765		
		Examiner Name	NORTON, NADINE G.		
Sheet	1	of	1	Attorney Docket Number	LMRX-P032 / P1205

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
LV	1	LEI et al., "The Effect of Ash Processes on Inorganic Porous Low-k Materials," Honeywell Electronic Materials, 4 pp.	
LV	2	COLLINS et al., "Chapter 1: Plasmas for Fun and Profit: A Survey of an Enabling Technology," 1999, pp. 1-24.	
LV	3	COLLINS et al., "Chapter 3: The Wax and Wane of Plasma Technology in IC Manufacturing," 1999, pp. 1-30.	
LV	4	GUERRA et al., "Implementation of Plasma Processing into BEOL with Organic Low-k Dielectrics," 2002 Semiconductor Equipment and Materials International, 5 pp.	

Examiner Signature		Date Considered	3/2/06
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached. This collection of information is required by 37 CFR 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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ELECTRONIC INFORMATION DISCLOSURE STATEMENT

Electronic Version v18

Stylesheet Version v18.0

**Title of
Invention**

Methods for the optimization of substrate etching in a plasma processing system

Application Number : 10/804430
Confirmation Number: 7228
First Named Applicant: Jisoo Kim
Attorney Docket Number: LMRX-P032/P1205
Art Unit: 1765
Examiner: Nadine G Norton
Search string: (6518174).pn



US Patent Documents

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
LV	1	6518174	2003-02-11	Annapragada, et al.			

Signature

Examiner Name	Date
LAN VINH	3/2/06